

Dual 50MHz to 1000MHz High-Linearity, Serial/Analog-Controlled VGA

General Description

The MAX2064 high-linearity, dual analog variable-gain amplifier (VGA) operates in the 50MHz to 1000MHz frequency range. Each analog attenuator is controlled using an external voltage, or through the SPI-compatible interface using an on-chip 8-bit DAC.

Since each of the stages has its own external RF input and RF output, this component can be configured to either optimize noise figure (NF) (amplifier configured first) or OIP3 (amplifier last). The device's performance features include 24dB amplifier gain (amplifier only), 4.4dB NF at maximum gain (includes attenuator insertion losses), and a high OIP3 level of +41dBm. Each of these features makes the device an ideal VGA for multipath receiver and transmitter applications.

In addition, the device operates from a single +5V supply with full performance, or a +3.3V supply for an enhanced power-savings mode with lower performance. The device is available in a compact 48-pin TQFN package (7mm x 7mm) with an exposed pad. Electrical performance is guaranteed over the extended temperature range, from $T_C = -40^{\circ}C$ to $+85^{\circ}C$.

_Applications

IF and RF Gain Stages

Temperature-Compensation Circuits

WCDMA, TD-SCDMA, and cdma2000® Base Stations

GSM 850/GSM 900 EDGE Base Stations

WiMAX®, LTE, and TD-LTE Base Stations and Customer-Premise Equipment

Fixed Broadband Wireless Access

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Wireless Local Loop

_Features

- ♦ Independently Controlled Dual Paths
- ♦ 50MHz to 1000MHz RF Frequency Range
- ♦ Pin-Compatible Family Includes MAX2062 (Analog/Digital VGA) MAX2063 (Digital-Only VGA)
- ♦ 22dB (typ) Maximum Gain
- ♦ 0.19dB Gain Flatness Over 100MHz Bandwidth
- ♦ 33dB Gain Range
- ♦ 49dB Path Isolation (at 200MHz)
- ♦ Built-In 8-Bit DACs for Analog Attenuation Control
- ♦ Excellent Linearity at 200MHz (Configured with Amp Last)
 - +41dBm OIP3
 - +59dBm OIP2
 - +19dBm Output 1dB Compression Point
- ♦ 4.4dB Typical Noise Figure (at 200MHz)
- ♦ Single +5V Supply (or +3.3V Operation)
- ♦ Amplifier Power-Down Mode for TDD Applications

Ordering Information

PART	TEMP RANGE	PIN-PACKAGE
MAX2064ETM+	-40°C to +85°C	48 TQFN-EP*
MAX2064ETM+T	-40°C to +85°C	48 TQFN-EP*

⁺Denotes a lead(Pb)-free/RoHS-compliant package.

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WiMAX is a registered certification mark and registered service mark of the WiMAX Forum.

^{*}EP = Exposed pad.

T = Tape and reel.

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ABSOLUTE MAXIMUM RATINGS

	_	
VCC_AMP_1, VCC_AM	MP_2, VCC_RG to GNI	O0.3V to +5.5V
PD_1, PD_2, AMPSE	ET to GND	0.3V to +3.6V
		0.3V to +3.6V
DAT, CS, CLK, AA_	SP to GND	0.3V to +3.6V
AMP_IN_1, AMP_IN	_2 to GND	+0.95V to +1.2V
AMP_OUT_1, AMP_	OUT_2 to GND	0.3V to +5.5V
A_ATT_IN_1, A_ATT	_IN_2, A_ATT_OUT_	1,
A_ATT_OUT_2 to	GND	0V to +3.6V
REG_OUT to GND		0.3V to +3.6V
RF Input Power (A_A	ATT_IN_1, A_ATT_IN	_2)+20dBm

RF Input Power (AMP_IN_1, AMP_IN_2)	+18dBm
θ _{JC} (Notes 1, 2)	+12.3°C/W
θJA (Notes 2, 3)	+38°C/W
Continuous Power Dissipation (Note 1)	5.3W
Operating Case Temperature Range (Note 4)	40°C to +85°C
Junction Temperature	+150°C
Storage Temperature Range	-65°C to +150°C
Lead Temperature (soldering, 10s)	+300°C
Soldering Temperature (reflow)	+260°C

- Note 1: Based on junction temperature T_J = T_C + (θ_JC x V_CC x I_CC). This formula can be used when the temperature of the exposed pad is known while the device is soldered down to a PCB. See the *Applications Information* section for details. The junction temperature must not exceed +150°C.
- **Note 2:** Package thermal resistances were obtained using the method described in JEDEC specification JESD51-7, using a four-layer board. For detailed information on package thermal considerations, refer to **www.maximintegrated.com/thermal-tutorial**.
- Note 3: Junction temperature T_J = T_A + (θ_{JA} x V_{CC} x I_{CC}). This formula can be used when the ambient temperature of the PCB is known. The junction temperature must not exceed +150°C.
- Note 4: To is the temperature on the exposed pad of the package. TA is the ambient temperature of the device and PCB.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

+5V SUPPLY DC ELECTRICAL CHARACTERISTICS

(Typical Application Circuit, $V_{CC} = V_{CC_AMP_1} = V_{CC_AMP_2} = V_{CC_RG} = +4.75V$ to +5.25V, AMPSET = 0, PD_1 = PD_2 = 0, T_C = -40°C to +85°C. Typical values are at $V_{CC} = +5.0V$ and $T_{C} = +25$ °C, unless otherwise noted.)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Supply Voltage	Vcc		4.75	5	5.25	V
Supply Current	IDC			143	210	mA
Power-Down Current	IDCPD	PD_1 = PD_2 = 1, V _{IH} = 3.3V		5.3	8	mA
Input Low Voltage	VIL				0.5	V
Input High Voltage	VIH		1.7		3.465	V
Input Logic Current	I _{IH} , I _{IL}		-1		+1	μΑ

+3.3V SUPPLY DC ELECTRICAL CHARACTERISTICS

(Typical Application Circuit, $V_{CC} = V_{CC_AMP_1} = V_{CC_AMP_2} = V_{CC_RG} = +3.135V$ to +3.465V, AMPSET = 1, PD_1 = PD_2 = 0, TC = -40°C to $+85^{\circ}$ C. Typical values are at $V_{CC_} = +3.3V$ and TC = $+25^{\circ}$ C, unless otherwise noted.)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Supply Voltage	Vcc		3.135	3.3	3.465	V
Supply Current	IDC			84.7	145	mA
Power-Down Current	IDCPD	PD_1 = PD_2 = 1, V _{IH} = 3.3V		4.5	8	mA
Input Low Voltage	VIL			0.5		V
Input High Voltage	VIH			1.7		V

RECOMMENDED AC OPERATING CONDITIONS

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
RF Frequency	fRF	(Note 5)	50		1000	MHz

+5V SUPPLY AC ELECTRICAL CHARACTERISTICS (each path, unless otherwise noted)

(*Typical Application Circuit*, VCC = VCC_AMP_1 = VCC_AMP_2 = VCC_RG = +4.75V to +5.25V, attenuators are set for maximum gain, RF ports are driven from 50Ω sources, AMPSET = 0, PD_1 = PD_2 = 0, $100MHz \le f_{RF} \le 500MHz$, $T_{C} = -40^{\circ}C$ to +85°C. Typical values are at maximum gain setting, $V_{CC} = +5.0V$, $P_{IN} = -20dBm$, $f_{RF} = 350MHz$, and $T_{C} = +25^{\circ}C$, unless otherwise noted.) (Note 6)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS	
		fRF = 50MHz		22.4			
		f _{RF} = 100MHz		22.3			
		f _{RF} = 200MHz		22.2			
Small-Signal Gain	G	$f_{RF} = 350MHz, T_{C} = +25^{\circ}C$	19.5	21.9	23.5	dB	
		fRF = 450MHz		21.7			
		f _{RF} = 750MHz		21.4			
		f _{RF} = 900MHz		20.6			
Gain vs. Temperature				-0.006		dB/°C	
		From 100MHz to 200MHz		0.18			
Gain Flatness vs. Frequency		Any 100MHz frequency band from 200MHz to 500MHz		0.19		dB	
		f _{RF} = 50MHz		4.4			
		f _{RF} = 100MHz		4.4			
		fRF = 200MHz		4.4			
Noise Figure	NF	f _{RF} = 350MHz		4.6		dB	
		fRF = 450MHz		4.7			
		f _{RF} = 750MHz		5.3			
		f _{RF} = 900MHz		5.7			
Total Attenuation Range		$f_{RF} = 350MHz, T_{C} = +25^{\circ}C$	30	32.9		dB	
Output Second-Order Intercept Point	OIP2	$P_{OUT} = 0dBm/tone$, $\Delta f = 1MHz$, $f_1 + f_2$		53.7		dBm	
Data laglation		RF input 1 amplified power measured at RF output 2 relative to RF output 1, all unused ports terminated to 50Ω		48.7		dB	
Path Isolation		RF input 2 amplified signal measured at RF output 1 relative to RF output 2, all unused ports terminated to 50Ω		48.6		ав	
		Pout = 0dBm/tone, $\Delta f = 1MHz$, fRF = 50MHz		46.3			
		Pout = 0dBm/tone, Δf = 1MHz, f_{RF} = 100MHz		44.2		dBm	
		Pout = 0dBm/tone, Δf = 1MHz, fRF = 200MHz		41.1			
Output Third-Order Intercept Point	OIP3	Pout = 0dBm/tone, Δf = 1MHz, f_{RF} = 350MHz		37.1			
		Pout = 0dBm/tone, Δf = 1MHz, f _{RF} = 450MHz		34.9			
		Pout = 0dBm/tone, Δf = 1MHz, f_{RF} = 750MHz		28.2			
		Pout = 0dBm/tone, Δf = 1MHz, f _{RF} = 900MHz		24.6			

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+5V SUPPLY AC ELECTRICAL CHARACTERISTICS (each path, unless otherwise noted) (continued)

(Typical Application Circuit, VCC = VCC_AMP_1 = VCC_AMP_2 = VCC_RG = +4.75V to +5.25V, attenuators are set for maximum gain, RF ports are driven from 50Ω sources, AMPSET = 0, PD_1 = PD_2 = 0, $100MHz \le f_{RF} \le 500MHz$, $T_{C} = -40^{\circ}C$ to +85°C. Typical values are at maximum gain setting, VCC = +5.0V, $P_{IN} = -20dBm$, $f_{RF} = 350MHz$, and $T_{C} = +25^{\circ}C$, unless otherwise noted.) (Note 6)

PARAMETER	SYMBOL		CONDITIONS	MIN	TYP	MAX	UNITS
Output -1dB Compression Point	P _{1dB}	$f_{RF} = 350MHz,$	T _C = +25°C (Note 7)	17	18.7		dBm
Second Harmonic		POUT = +3dBm			-56.7		dBc
Third Harmonic		POUT = +3dBm			-72.4		dBc
Group Delay		Includes EV kit	PCB delays		0.9		ns
Amplifier Power-Down Time			rom 0 to 1, amplifier DC settles to within 0.1mA		0.5		μs
Amplifier Power-Up Time			rom 1 to 0, amplifier DC settles to within 1%		0.5		μs
Input Return Loss	RLIN	50Ω source			16.8		dB
Output Return Loss	RLOUT	50Ω load			30.7		dB
ANALOG ATTENUATOR (each p	ath, unless o	otherwise noted					
Insertion Loss	IL				2.2		dB
Input Second-Order Intercept Point	IIP2	$P_{IN1} = 0dBm, P_{attenuation}, \Delta f$	IN2 = 0dBm (minimum = 1MHz, f ₁ + f ₂		61.9		dBm
Input Third-Order Intercept Point	IIP3	$P_{IN1} = 0dBm, P_{attenuation}, \Delta f$	IN2 = 0dBm (minimum = 1MHz	37.0			dBm
Attenuation Range					32.9		dB
Gain Control Slope		Analog control i	nput		-13.3		dB/V
Maximum Gain Control Slope		Over analog co	ntrol input range		-35.2		dB/V
Insertion Phase Change		Over analog co	ntrol input range	16.5			Deg/V
			31dB to 0dB, AA_SP = 0, from A_VCTL_ step		500		
A.,		RF settled to	31dB to 0dB, AA_SP = 1, from $\overline{\text{CS}}$ step		500		
Attenuator Response Time		within ±0.5dB	0dB to 31dB, AA_SP = 0, from A_VCTL_ step		500		ns
			OdB to 31dB, AA_SP = 1, from $\overline{\text{CS}}$ step		500		
Group Delay vs. Control Voltage		Over analog col	ntrol input from 0.25V to		-0.26		ns
Analog Control Input Range				0.25		2.75	V
Analog Control Input Impedance					19.2		kΩ
Input Return Loss		50Ω source			16.0		dB
Output Return Loss		50Ω load			15.9		dB

+5V SUPPLY AC ELECTRICAL CHARACTERISTICS (each path, unless otherwise noted) (continued)

(*Typical Application Circuit*, VCC = VCC_AMP_1 = VCC_AMP_2 = VCC_RG = +4.75V to +5.25V, attenuators are set for maximum gain, RF ports are driven from 50Ω sources, AMPSET = 0, PD_1 = PD_2 = 0, $100MHz \le f_{RF} \le 500MHz$, $T_{C} = -40^{\circ}C$ to +85°C. Typical values are at maximum gain setting, $V_{CC} = +5.0V$, $P_{IN} = -20dBm$, $f_{RF} = 350MHz$, and $T_{C} = +25^{\circ}C$, unless otherwise noted.) (Note 6)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
D/A CONVERTER			•			
Number of Bits				8		Bits
		DAC code = 00000000			0.35	V
Output Voltage		DAC code = 11111111	2.7]
SERIAL PERIPHERAL INTERF	ACE (SPI)		•			
Maximum Clock Speed				20		MHz
Data-to-Clock Setup Time	tcs			2		ns
Data-to-Clock Hold Time	tCH			2.5		ns
Clock-to-CS Setup Time	tES			3		ns
CS Positive Pulse Width	tEW			7		ns
CS Setup Time	tews			3.5		ns
Clock Pulse Width	tcw			5		ns

+3.3V SUPPLY AC ELECTRICAL CHARACTERISTICS (each path, unless otherwise noted)

(*Typical Application Circuit*, VCC = VCC_AMP_1 = VCC_AMP_2 = VCC_RG = +3.135V to +3.465V, attenuators are set for maximum gain, RF ports are driven from 50Ω sources, AMPSET = 1, PD_1 = PD_2 = 0, $100MHz \le f_{RF} \le 500MHz$, $T_C = -40^{\circ}C$ to $+85^{\circ}C$. Typical values are at maximum gain setting, $V_{CC} = +3.3V$, $P_{IN} = -20dBm$, $f_{RF} = 350MHz$, and $T_{C} = +25^{\circ}C$, unless otherwise noted.) (Note 6)

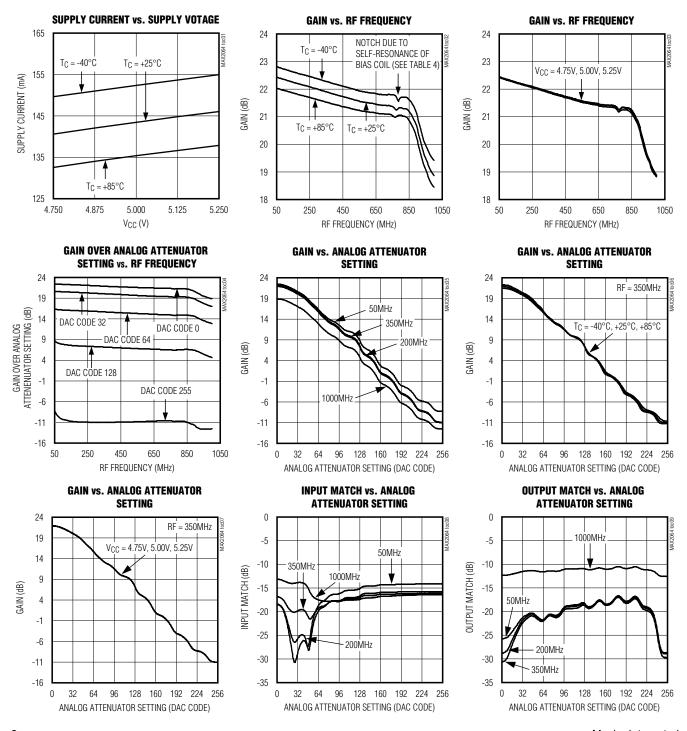
PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Small-Signal Gain	G			21.8		dB
Output Third-Order Intercept Point	OIP3	Pout = 0dBm/tone		29.1		dBm
Noise Figure	NF			4.8		dB
Total Attenuation Range				32.9		dB
Dath laciation		RF input 1 amplified power measured at RF output 2 relative to RF output 1, all unused ports terminated to 50Ω		48.1		dD
Path Isolation		RF input 2 amplified signal measured at RF output 1 relative to RF output 2, all unused ports terminated to 50Ω		48.2		dB
Output -1dB Compression Point	P _{1dB}	(Note 7)		13.2		dBm

- **Note 5:** Operation outside this range is possible, but with degraded performance of some parameters. See the *Typical Operating Characteristics*.
- **Note 6:** All limits include external component losses. Output measurements are performed at the RF output port of the *Typical Application Circuit*.
- Note 7: It is advisable not to continuously operate the RF input 1 or RF input 2 above +15dBm.

ual 50MHz to 1000MHz High-Linearity, Serial/Analog-Controlled VGA

Typical Operating Characteristics

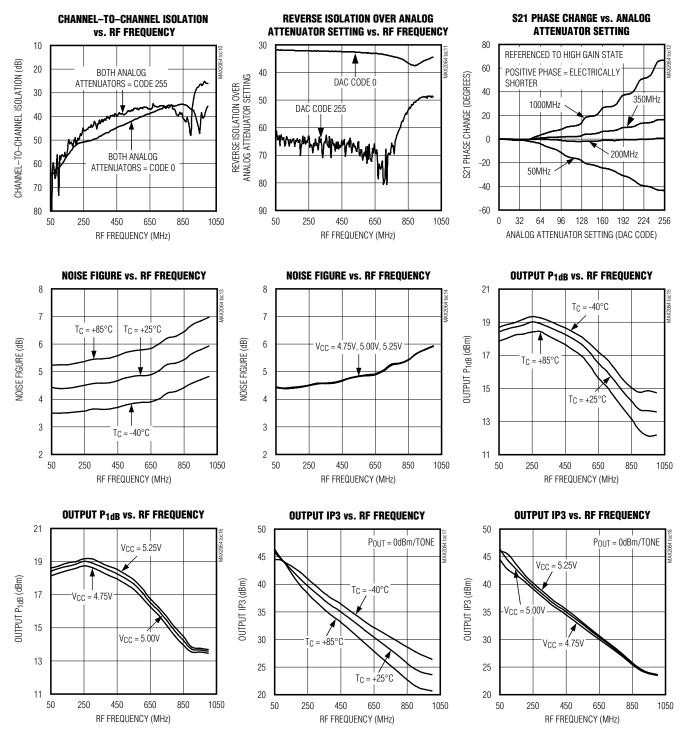
(*Typical Application Circuit*, **Vcc = Vcc_AMP_1 = Vcc_AMP_2 = Vcc_Rg = +5V**, attenuators are set for maximum gain, RF ports are driven from 50Ω sources, AMPSET = 0, PD_1 = PD_2 = 0, P_{IN} = -20dBm, f_{RF} = 350MHz, and T_C = +25°C, unless otherwise noted.)



Dual 50MHz to 1000MHz High-Linearity, Serial/Analog-Controlled VGA

Typical Operating Characteristics (continued)

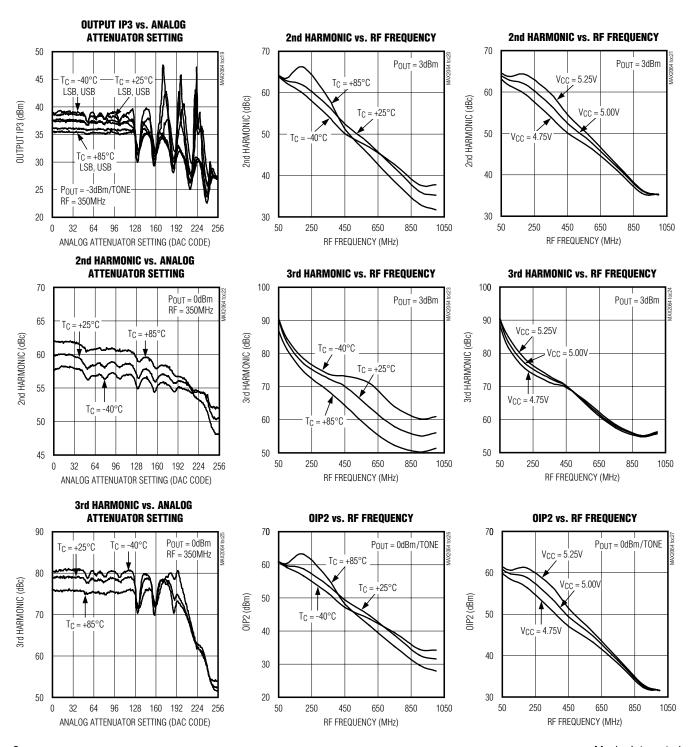
(*Typical Application Circuit*, $VCC = VCC_AMP_1 = VCC_AMP_2 = VCC_RG = +5V$, attenuators are set for maximum gain, RF ports are driven from 50Ω sources, AMPSET = 0, PD_1 = PD_2 = 0, P_{IN} = -20dBm, f_{RF} = 350MHz, and T_C = +25°C, unless otherwise noted.)



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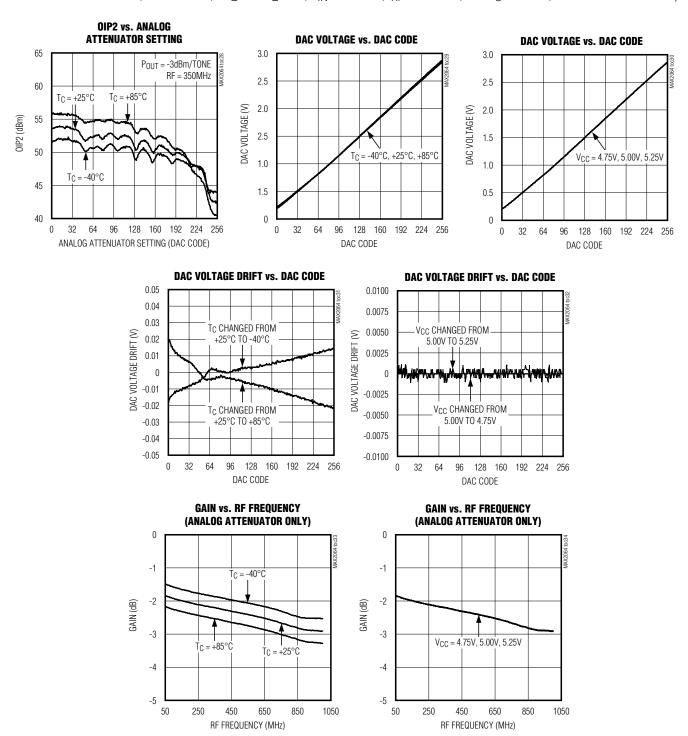
Typical Operating Characteristics (continued)

(*Typical Application Circuit*, $V_{CC} = V_{CC_AMP_1} = V_{CC_AMP_2} = V_{CC_RG} = +5V$, attenuators are set for maximum gain, RF ports are driven from 50 Ω sources, AMPSET = 0, PD_1 = PD_2 = 0, PlN = -20dBm, fRF = 350MHz, and T_C = +25°C, unless otherwise noted.)



Typical Operating Characteristics (continued)

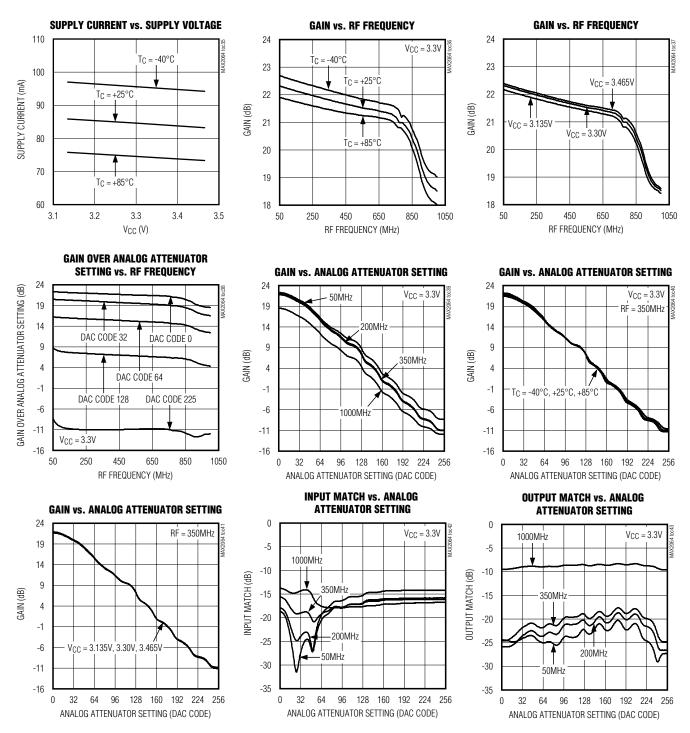
(*Typical Application Circuit*, $V_{CC} = V_{CC_AMP_1} = V_{CC_AMP_2} = V_{CC_RG} = +5V$, attenuators are set for maximum gain, RF ports are driven from 50Ω sources, AMPSET = 0, PD_1 = PD_2 = 0, P_{IN} = -20dBm, f_{RF} = 350MHz, and T_C = +25°C, unless otherwise noted.)



ual 50MHz to 1000MHz High-Linearity, Serial/Analog-Controlled VGA

Typical Operating Characteristics (continued)

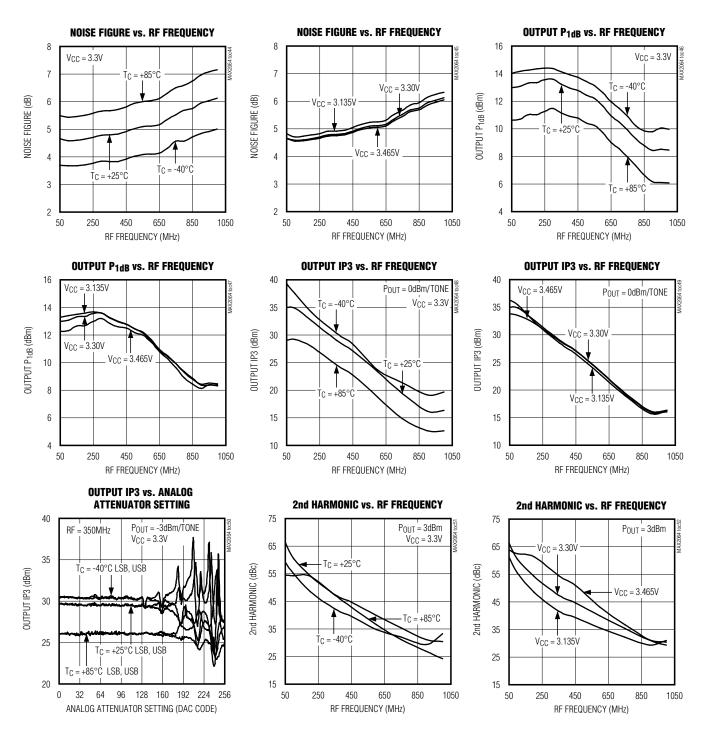
(*Typical Application Circuit*, $V_{CC} = V_{CC_AMP_1} = V_{CC_AMP_2} = V_{CC_RG} = +3.3V$, attenuators are set for maximum gain, RF ports are driven from 50 Ω sources, AMPSET = 1, PD_1 = PD_2 = 0, P_{IN} = -20dBm, f_{RF} = 350MHz, and T_C = +25°C, unless otherwise noted.)



Dual 50MHz to 1000MHz High-Linearity, Serial/Analog-Controlled VGA

Typical Operating Characteristics (continued)

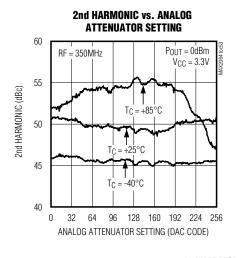
(*Typical Application Circuit*, Vcc = Vcc_AMP_1 = Vcc_AMP_2 = Vcc_RG = +3.3V, attenuators are set for maximum gain, RF ports are driven from 50Ω sources, AMPSET = 1, PD_1 = PD_2 = 0, P_{IN} = -20dBm, f_{RF} = 350MHz, and T_C = +25°C, unless otherwise noted.)

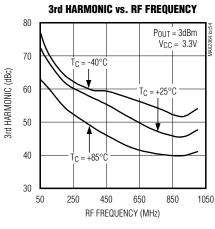


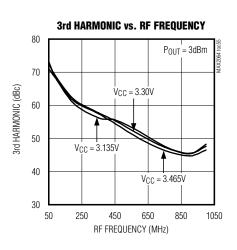
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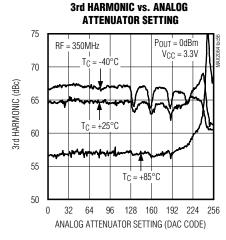
Typical Operating Characteristics (continued)

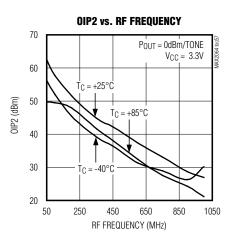
(*Typical Application Circuit*, $V_{CC} = V_{CC_AMP_1} = V_{CC_AMP_2} = V_{CC_RG} = +3.3V$, attenuators are set for maximum gain, RF ports are driven from 50Ω sources, AMPSET = 1, PD_1 = PD_2 = 0, PIN = -20dBm, fRF = 350MHz, and TC = +25°C, unless otherwise noted.)

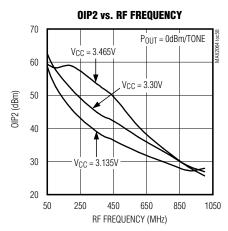


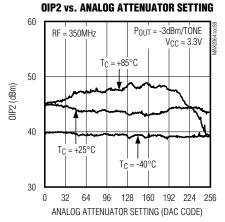






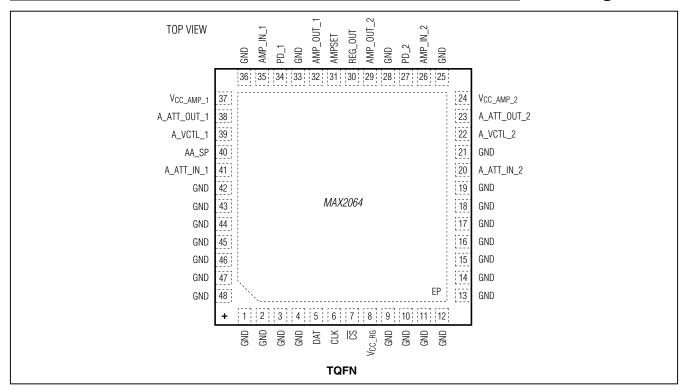






Dual 50MHz to 1000MHz High-Linearity, Serial/Analog-Controlled VGA

Pin Configuration



Pin Description

PIN	NAME	FUNCTION
1–4, 9–19, 21, 25, 28, 33, 36, 42–48	GND	Ground
5	DAT	SPI Data Digital Input
6	CLK	SPI Clock Digital Input
7	CS	SPI Chip-Select Digital Input
8	VCC_RG	Regulator Supply Input. Connect to a 3.3V or 5V external power supply. V _{CC_RG} powers all circuits except for the driver amplifiers. Bypass with a 10nF capacitor as close as possible to the pin.
20	A_ATT_IN_2	Analog Attenuator Input (50Ω), Path 2. Requires a 1000pF DC-blocking capacitor.
22	A_VCTL_2	Analog Attenuator Voltage-Control Input, Path 2. Bypass to ground with a 150pF capacitor if DAC 2 is used (AA_SP = 1).
23	A_ATT_OUT_2	Analog Attenuator Output (50 Ω), Path 2. Requires a DC-blocking capacitor. Connect to AMP_IN_2 through a 1000pF capacitor.
24	VCC_AMP_2	Driver Amplifier Supply-Voltage Input, Path 2. Bypass with a 10nF capacitor as close as possible to the pin.
26	AMP_IN_2	Driver Amplifier Input (50Ω), Path 2. Requires a DC-blocking capacitor. Connect to A_ATT_OUT_2 through a 1000pF capacitor.
27	PD_2	Power-Down, Path 2. See Table 2 for operation details.
29	AMP_OUT_2	Driver Amplifier Output (50 Ω), Path 2. Connect a pullup inductor from AMP_OUT_2 to VCC

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Pin Description (continued)

PIN	NAME	FUNCTION
30	REG_OUT	Regulator Output. Bypass with 1µF capacitor.
31	AMPSET	Driver Amplifier Bias Setting for 3.3V Operation. Set to logic 1 for 3.3V operation on pins VCC_AMP_1 and VCC_AMP_2. Set to logic 0 for 5V operation.
32	AMP_OUT_1	Driver Amplifier Output (50Ω), Path 1. Connect a pullup inductor from AMP_OUT_1 to V _{CC}
34	PD_1	Power-Down, Path 1. See Table 2 for operation details.
35	AMP_IN_1	Driver Amplifier Input (50Ω), Path 1. Requires a DC-blocking capacitor. Connect to A_ATT_OUT_1 through a 1000pF capacitor.
37	VCC_AMP_1	Driver Amplifier Supply Voltage Input, Path 1. Bypass with a 10nF capacitor as close as possible to the pin.
38	A_ATT_OUT_1	Analog Attenuator Output (50 Ω), Path 1. Requires a DC-blocking capacitor. Connect to AMP_IN_1 through a 1000pF capacitor.
39	A_VCTL_1	Analog Attenuator Voltage-Control Input, Path 1. Bypass to ground with a 150pF capacitor if on-chip DAC is used (AA_SP = 1).
40	AA_SP	DAC Enable/Disable Logic Input for Analog Attenuators. Set AA_SP to logic 1 to enable on-chip DAC circuit and digital SPI control. Set AA_SP to logic 0 to disable DAC circuit and digital SPI control. When AA_SP = 0, use analog control lines (A_VCTL_1 and A_VCTL_2).
41	A_ATT_IN_1	Analog Attenuator Input (50Ω), Path 1. Requires a 1000pF DC-blocking capacitor.
_	EP	Exposed Pad. Internally connected to GND. Connect to a large PCB ground plane for proper RF performance and enhanced thermal dissipation.

Detailed Description

The MAX2064 high-linearity analog VGA is a general-purpose, high-performance amplifier designed to interface with 50Ω systems operating in the 50MHz to 1000MHz frequency range.

Each channel of the device integrates an analog attenuator to provide 33dB of total gain control, as well as a driver amplifier optimized to provide high gain, high IP3, low NF, and low power consumption.

Each analog attenuator is controlled using an external voltage or through the SPI-compatible interface using an on-chip 8-bit DAC. See the *Applications Information* section and Table 3 for attenuator programming details.

Because each of the two stages in the separate signal paths has its own RF input and RF output, this component can be configured to either optimize NF (amplifier configured first) or OIP3 (amplifier last). The device's performance features include 24dB amplifier gain (amplifier only), 4.4dB NF at maximum gain (includes attenuator insertion losses), and a high OIP3 level of +41dBm. Each of these features makes the device an ideal VGA for multipath receiver and transmitter applications.

In addition, the device operates from a single +5V supply with full performance, or a +3.3V supply for an enhanced power-savings mode with lower performance. The device is available in a compact 48-pin TQFN package (7mm x 7mm) with an exposed pad. Electrical performance is guaranteed over the extended temperature range, from $T_C = -40$ °C to +85°C.

Analog Attenuator Control

The device integrates two analog attenuators. Each analog attenuator has a 33dB range and is controlled using an external voltage, or through the 3-wire SPI interface using an on-chip 8-bit DAC. See the *Applications Information* section and Table 3 for attenuator programming details. The attenuators can be used for both static and dynamic power control.

Note that when the analog attenuators are controlled by the DACs through the SPI bus, the DAC output voltage shows on A_VCTL_1 and A_VCTL_2 (pins 39 and 22, respectively). Therefore, in SPI mode, the A_VCTL_1 and A_VCTL_2 pins must only connect to the resistor **and** capacitor to ground, as shown in the *Typical Application Circuit*.

Table 1. Control Logic

AA_SP	ANALOG ATTENUATOR	D/A CONVERTER
0	Controlled by external control voltage	Disabled
1	ICantrolled by on-chin DAC	Enabled (DAC output voltage shows on A_VCTL pins); DAC uses on-chip voltage reference

Table 2. Operating Modes

RESULT	V _{CC} (V)	AMP_SET	PD_1	PD_2
All on	5	0	0	0
All Off	3.3	1	0	0
AMP1 off	5	0	1	0
AMP2 on	3.3	1	1	0
AMP1 on	5	0	0	1
AMP2 off	3.3	1	0	1
All off	5	0	1	1
All Oll	3.3	1	1	1

Driver Amplifier

Each path of the device includes a high-performance driver with a fixed gain of 24dB. The driver amplifier circuits are optimized for high linearity for the 50MHz to 1000MHz frequency range.

Applications Information

Operating Modes

The device features an optional +3.3V supply voltage operation with reduced linearity performance. The AMPSET pin needs to be biased accordingly in each mode, as listed in Table 2. In addition, the driver amplifiers can be shut down independently to conserve DC power. See the biasing scheme outlined in Table 2 for details.

SPI Interface and Attenuator Settings

The attenuators can be programmed through the 3-wire SPI/MICROWIRETM-compatible serial interface using 5-bit words. Fifty-six bits of data are shifted in MSB first and are framed by $\overline{\text{CS}}$. The first 28 bits set the first attenuator and the following 28 bits set the second attenuator. When $\overline{\text{CS}}$ is low, the clock is active and data is shifted on the rising edge of the clock. When $\overline{\text{CS}}$ transitions high, the data is latched and the attenuator setting changes (Figure 1). See Table 3 for details on the SPI data format.

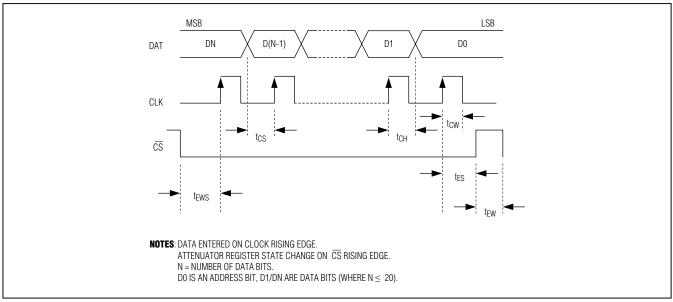


Figure 1. SPI Timing Diagram

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ual 50MHz to 1000MHz High-Linearity, Serial/Analog-Controlled VGA

Table 3. SPI Data Format

FUNCTION	BIT	DESCRIPTION		
	D55 (MSB)			
	D54			
	D53			
	D52			
	D51			
	D50			
	D49			
	D48			
	D47			
Reserved	D46	Bits D[55:36] are reserved. Set to logic 0.		
neserveu	D45	Talls D[33.30] are reserved. Set to logic 0.		
	D44			
	D43			
	D42			
	D41			
	D40			
	D39			
	D38			
	D37			
	D36			
	D35	Bit 7 (MSB) of on-chip DAC used to program the Path 2 analog attenuator		
	D34	Bit 6 of DAC		
	D33	Bit 5 of DAC		
On-Chip DAC	D32	Bit 4 of DAC		
(Path 2)	D31	Bit 3 of DAC		
	D30	Bit 2 of DAC		
	D29	Bit 1 of DAC		
	D28	Bit 0 (LSB) of DAC		

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Table 3. SPI Data Format (continued)

FUNCTION	BIT	DESCRIPTION			
	D27				
	D26				
	D25				
	D24				
	D23				
	D22				
	D21				
	D20				
	D19				
Reserved	D18	Pita D[07:0] are recorded. Set to logic 0			
neserveu	D17	Bits D[27:8] are reserved. Set to logic 0.			
	D16				
	D15				
	D14				
	D13				
	D12				
	D11				
	D10				
	D9				
	D8				
	D7	Bit 7 (MSB) of on-chip DAC used to program the Path 1 analog attenuator			
	D6	Bit 6 of DAC			
	D5	Bit 5 of DAC			
On-Chip DAC	D4	Bit 4 of DAC			
(Path 1)	D3	Bit 3 of DAC			
	D2	Bit 2 of DAC			
	D1	Bit 1 of DAC			
	D0 (LSB)	Bit 0 (LSB) of DAC			

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Power-Supply Sequencing

The sequence to be used is:

- 1) Power supply
- 2) Control lines

Layout Considerations

The pin configuration of the device is optimized to facilitate a very compact physical layout of the device and its associated discrete components. The exposed pad (EP) of the device's 48-pin TQFN-EP package provides a low thermal-resistance path to the die. It is important that

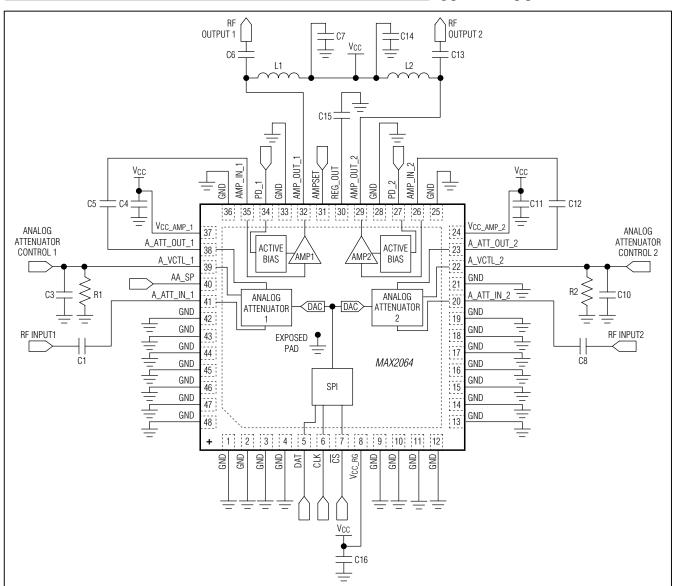
the PCB on which the device is mounted be designed to conduct heat from the EP. In addition, provide the EP with a low inductance path to electrical ground. The EP **MUST** be soldered to a ground plane on the PCB, either directly or through an array of plated via holes. The layout of the PCB should include proper top-layer ground shielding to isolate the amplifier's inputs and outputs from each other. Shielding between the paths (inputs and outputs) is important for channel-to-channel isolation.

Table 4. Typical Application Circuit Component Values

DESIGNATION	QTY	DESCRIPTION	COMPONENT SUPPLIER	
C1, C5, C6, C8, C12, C13	6	1000pF ceramic capacitors (0402) GRM1555C1H102J	Murata Electronics North America, Inc.	
C3, C10	2	150pF ceramic capacitors (0402) GRM1555C1H151J	Murata Electronics North America, Inc.	
C4, C7, C11, C14, C16	5	10nF ceramic capacitors (0402) GRM155R71E103K	Murata Electronics North America, Inc.	
C15	1	1µF ceramic capacitor (0603) GRM188R71C105K	Murata Electronics North America, Inc.	
L1, L2*	2	820nH inductors (1008) Coilcraft 1008CS-821XJLC	Coilcraft, Inc.	
R1, R2	2	47.5kΩ resistors (0402)	_	
U1	1	1 48 TQFN-EP (7mm x 7mm) Maxim MAX2064ETM+ Maxim Integrated Products		

^{*}Select the inductors to ensure that self-resonance of the inductors is outside the band of operation.

Typical Application Circuit



Chip Information

PROCESS: SiGe BiCMOS

Package Information

For the latest package outline information and land patterns, go to www.maximintegrated.com/packages. Note that a "+", "#", or "-" in the package code indicates RoHS status only. Package drawings may show a different suffix character, but the drawing pertains to the package regardless of RoHS status.

PACKAGE	PACKAGE	OUTLINE	LAND
TYPE	CODE	NO.	PATTERN NO.
48 TQFN-EP	T4877+7	21-0144	

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Revision History

REVISION NUMBER	REVISION DATE	DESCRIPTION	PAGES CHANGED
0	12/10	Initial release	_
1	8/15	Removed military reference from Applications	1



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